Please amend the claims as follows:

1. (Currently amended) A high frequency component with a substrate constructed of a plurality of dielectric layers and, between them, electrode layers having conducting track structures, the substrate including a resonator element having at least one capacitive element and at least one inductive element formed by at least one arrangement of opposed conducting track structures, the opposed conducting track structures being separated by a dielectric layer having a thickness that is smaller than the width of either of the opposed conducting track structures, the dielectric layer having a dielectric constant and thickness selected such that the common-mode impedance and the push-pull impedance between the opposed conducting track structures of the at least one arrangement differs by a factor of at least 2.

2. (Currently amended) A high frequency component according to claim 1, characterized in that the opposed conducting track structures of the at least one arrangement are linked to each other at least at one site by a conductor or with fixed potentials.

3. (Currently amended) A high frequency component according to claim 1, characterized in that the common-mode impedance of and the push-pull impedance between the ~~at least~~ two opposing conducting track structures of the at least one arrangement differ by a factor of at least 10.

4. (Cancelled).

5. (Currently amended) A high frequency component according to claim 1, characterized in that the thickness of the dielectric layer arranged between the opposed conducting track structures of the at least one arrangement ~~is smaller than one opposed conducting track structures of the at least one arrangement~~ is smaller than one fifth of the width of either of the opposed conducting track structures.

6. (Previously presented) A high frequency component according to claim 1,

characterized in that the dielectric layer between the opposed conducting track structures of the at least one arrangement has an increased dielectric constant compared with surrounding dielectric layers.

7. (Previously presented) A high frequency component according to claim 1, characterized in that the dielectric layer between the opposed conducting track structures of the at least one arrangement has a dielectric constant of greater than 5.

8. (Previously presented) A high frequency component according to claim 1, characterized in that the dielectric layer between the opposed conducting track structures of the at least one arrangement has a dielectric constant of greater than 70.

9. (Currently amended) A high frequency component according to claim 1, wherein the dielectric layer between the opposed conducting track structures of the at least one arrangement contains materials with barium-rare earth-titanium-perovskites, barium-strontium-titanates, bismuth pyrochlore structures, tantalum oxides, magnesium-aluminium-calcium-silicates, (calcium, strontium)-zirconates and/or magnesium titanates, also in combination with boron or lead silicate glasses.

10. (Original) A high frequency component according to claim 1, characterized in that the substrate is a ceramic laminate as a low temperature co-fired ceramics (LTCC) material or a high temperature co-fired ceramics (HTCC) material, an organic laminate, a semiconductor substrate or a substrate based on thin film technology.

11. (Currently amended) A high frequency component according to claim 1, characterized by a working frequency above about 400 MHz.

12. (Currently amended) A high frequency component according to claim 1, characterized in that the conducting track width of one of the opposed conducting track structures of the at least one arrangement is larger than that of the other opposed conducting track structure by a factor of 2k, where k is at least 70% of the sum of a layer offset v of the opposed conducting

track structures and half the thickness d of the dielectric layer situated between the opposed conducting track structures of the at least one arrangement.

13. (Currently amended) A high frequency component according to claim 1, characterized in that the opposed conducting track structures of the at least one arrangement each includes two sections running in the same direction, and wherein the two sections of one of the opposed conducting track structures have a separation that is larger than a separation between the two sections of the other of the opposed conducting track structures by a factor of 2k, whereby k is at least 50% of the sum of a layer offset v of the opposed conducting track structures and half the thickness d of the dielectric layer situated between the opposed conducting track structures of the at least one arrangement.

14. (Previously presented) A high frequency component according to claim 1, characterized in that the opposed conducting tracks of the at least one arrangement are coupled by a bridge or by a common conducting member.

15. (Previously presented) A high frequency component according to claim 14, characterized in that the bridge or the conducting member is a connection between two of the electrode layers.

16. (Previously presented) A resonator in a high frequency component according to claim 1, characterized in that each of the opposed conducting track structures of the at least one arrangement includes a start and an end defined by a current path, wherein the start of one of the opposed conducting tracks is placed at the same potential as the end of the other of the opposed conducting tracks, the remaining end of the one of the opposed conducting tracks and the remaining start of the other of the opposed conducting tracks being unconnected.

17. (Currently amended) A resonator in a high frequency component according to claim 16, characterized in that the start of the one opposed conducting track is connected to the end of the other opposed conducting track via a connecting conductor, the connecting conductor being a non-overlapping extension of the opposed conducting tracks and/or at least one lead-

through through at least one insulating layer disposed between the opposed conducting tracks of the at least one arrangement.

18. (Previously presented) A resonator in a high frequency component claim 1, characterized in that in the at least one arrangement of opposed conducting tracks, one start of one of the opposed conducting track and one end of the other of the opposed conducting tracks are connected to a fixed potential.

19. (Previously presented) A resonator according to claim 16, characterized in that the remaining unconnected end of the one of the opposed conducting tracks is placed at a fixed potential.

20. (Previously presented) A resonator according to claim 16, characterized in that the remaining unconnected end of the one of the opposed conducting tracks is extended with a conducting track extension and/or connected to earth with a capacitor.

21. (Currently amended) A resonator according to claim 16, characterized in that on at least one side of the opposed conducting track structures of the at least one arrangement, an earth surface is provided.

22. (Currently amended) A resonator according to claim 16, characterized in that the opposed conducting track structures of the at least one arrangement are surrounded by magnetic materials.

23. (Currently amended) A filter with at least one resonator element according to claim 16, whereby the input and output of signals and the coupling to the at least one resonator element takes place directly via a connection to the opposed conducting track structures, inductively through the conducting tracks of the at least one arrangement running parallel in places and/or capacitively via a capacitor.

24. (Currently amended) A filter with least two resonators elements according to claim 16,

whereby at least one coupling between the at least two resonators elements is generated through a common conducting track member connected to earth.

25. (Original) A balancing transformer (balun) having at least one resonator according to claim 16, whereby the input of signals takes place symmetrically and the output takes place asymmetrically.

26. (Currently amended) An adaptor network having at least one resonator according to claim 16, whereby the impedance of couplings between the opposed conducting track structures of the at least one arrangement is determined by the positioning of the couplings.

27. (Currently amended) A network with at least one resonator element according to claim 16, which performs the function of a filter, a balancing transformer and/or of an adaptor network.

28. (Original) A high frequency module with at least one of the components claimed in claim 1.

29. (Original) A high frequency module according to claim 28, which performs the function of a transmitting and receiving module.

30. (Previously presented) The high frequency component according to claim 1, wherein the resonator element has a conductor length that is less than a quarter wavelength for working frequencies above 400 MHz.

31. (Previously presented) The high frequency component according to claim 1, wherein the dielectric layer has a thickness of 25 μm or less.